EUROPEAN PATENT OFFICE

Abstracts of Japan

PUBLICATION NUMBER

02192110

PUBLICATION DATE

27-07-90

APPLICATION DATE

19-01-89

APPLICATION NUMBER

: 01012603

APPLICANT : FUJITSU LTD;

INVENTOR :

UEDA YOSHITO;

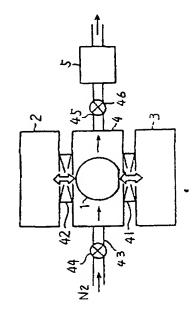
INT.CL.

H01L 21/02

TITLE

: MANUFACTURE OF

SEMICONDUCTOR DEVICE



ABSTRACT :

PURPOSE: To prevent adhesion of dust to the wafers to be processed and to the processed wafers by a method wherein ionized gas in blown against the wafers, and the electric charge of the electrostatically adhered dust is neutralized.

CONSTITUTION: A first gate 41 is provided between a reserve vacuum chamber 4 and a wafer cassette part 3, and a second gate 42 is provided between the reserve vacuum chamber 4 and a vacuum chamber 2. Also, a gas-introducing piping 43 is connected to one side face of the reserve vacuum chamber 4 through the intermediary of an ionizing device 6, and a gas exhausting piping 45 is connected to other side face of the reserve vacuum chamber 4. A first cock 44 is provided in the midway of the gas-introducing piping 43, a second cock 46 is provided midway on the gas-exhausting piping 45, and a vacuum pump 5 is connected thereto. In this case, ionized gas is blown against a wafer 1 which passes through the reserve vacuum chamber 45, the electric charge of dust is neutralized electrostatically. As a result, the generation of a throw vent can be prevented, and the quantity of dust adhered to the wafer can also be reduced.

COPYRIGHT: (C)1990,JPO&Japio